

Table of Contents

Stable Hydrogen Pair Trapped at Carbon Impurities in Silicon V.P. Markevich, B. Hourahine, R.C. Newman, R. Jones, M. Kleverman, J.L. Lindström, L.I. Murin, M. Suezawa, S. Öberg and P.R. Briddon	1
New Approach to Capacitance Studies of 'DX' Centers L. Dózsa	11
Diodes Fabricated by Electron Beam Doping (Superdiffusion) Technique in Semiconductors at Room Temperature T. Wada and H. Fujimoto	23
Modeling of Dopant and Defect Interactions in Si Process Simulators L. Pelaz, L.A. Marqués, M. Aboy and J. Barbolla	31
Spectroscopic Study of Magnesium-Related Impurities in Silicon L.T. Ho	41
Makyoh Topography: A Simple Yet Powerful Optical Method for Surface Flatness and Defect Characterisation F. Riesz	51
Electron Diffraction of 3-D Defects in Nanostructural II-VI Semiconductors M. Kuzma	63
A Finite Difference Calculation of Impurity Migration in Semiconductors by the Kick-Out Mechanism A. Benmakhlouf	89
In-Diffusion Concentration Profiles of Dopants in Semiconductors E. Antoncik	109
Recent Advances in the Measurement of Interstitial Oxygen in Silicon by Infra-Red Spectroscopy B. Pivac, A. Sassella and A. Borghesi	123
Algorithm Animation for Superdiffusion of a Non-Equilibrium in Semiconductors T. Wada and H. Nagao	133
Abstracts	1